

# **Chip Integration Technology Corporation**

Super Low Barrier High Voltage Power Rectifier

#### Main Product Characteristics

I <sub>F(AV)</sub>	10A
V <sub>RRM</sub>	45V
T <sub>J</sub>	150°C
$V_{(Typ)}$	0.35V

### ■ Features

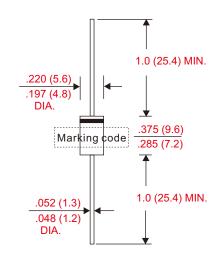
- Axial lead type devices for through hole design.
- Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CSRS1045G-A.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

### ■ Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case: Molded plastic, DO-201AD / DO-27
- Lead: Axial leads, solderable per MIL-STD-202, Method 208 guranteed
- Polarity: Color band denotes cathode end
- Weight : Approximated 1.10 gram
- Maximum ratings and electrical characteristics

Outline

DO-27(DO-201AD)



Dimensions in inches and (millimeters)

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CSRS1045-A	LINUT
Marking code			CSRS1045	UNIT
Peak repetitive reverse voltage		V <sub>RRM</sub>		
Working peak reverse voltage		V <sub>RWM</sub>	45	V
DC blocking voltage		V <sub>RM</sub>		
RMS reverse voltage		V <sub>R(RMS)</sub>	32	А
Forward rectified current		I <sub>o</sub>	10	А
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I <sub>FSM</sub>	300	А
Non-repetitive avalanche energy	T <sub>J</sub> = 25°C, I <sub>AS</sub> = 20A, L = 8.5mH	E <sub>AS</sub>	20	mJ
Thermal resistance	Junction to case	R <sub>eJC</sub>	4	°C/W
Operating and Storage temperature		T <sub>J</sub> , T <sub>STG</sub>	-55 ~ +150	°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Reverse breakdown voltage	I <sub>R</sub> = 0.5mA	$V_{\scriptscriptstyle (BR)R}$	45			V
Forward voltage drop	$I_F = 8A, T_J = 25^{\circ}C$				420	mV
	$I_F = 10A, T_J = 25^{\circ}C$	V <sub>F</sub>			470	
	$I_F = 10A, T_J = 125^{\circ}C$			350	410	
Reverse current	$V_R = V_{RRM} T_J = 25^{\circ}C$				0.3	mA
	$V_R = V_{RRM} T_J = 100^{\circ}C$	I <sub>R</sub>			15	
	$V_R = V_{RRM} T_J = 150^{\circ}C$				75	

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## ■ Rating and characteristic curves

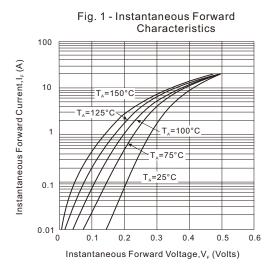


Fig. 2 - Reverse Characteristics

100

(YE)

10

T<sub>A</sub>=100°C

T<sub>A</sub>=75°C

0.01

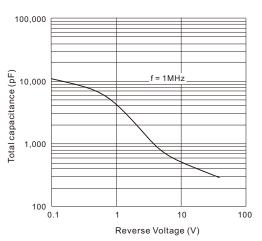
0.1

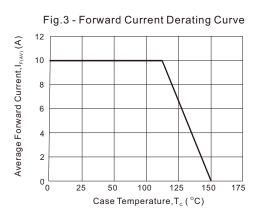
T<sub>A</sub>=25°C

0.01

Reverse Voltage, V<sub>R</sub> (V)

Fig. 3 - Total Capacitance VS. Reverse Voltage





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http://www.citcorp.com.tw/

Tel:886-3-5600628

Fax:886-3-5600636

Add:Rm. 3, 2F., No.32, Taiyuan St., Zhubei City, Hsinchu County 302, Taiwan (R.O.C.)

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